

N-Channel Enhancement Mode Power MOSFET

General Description

The HM75Nĭ Ĩ S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- $V_{DS}=75V$; $I_D=ĭ Ĩ A @ V_{GS}=10V$;
 $R_{DS(ON)} < 7m\Omega @ V_{GS}=10V$
- Special process technology for high ESD capability
- Special designed for Convertors and power controls
- High density cell design for ultra low R_{dson}
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

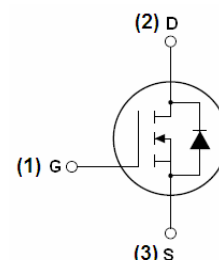
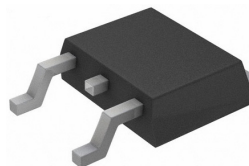
Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

Product Summary

BV_{DSS}	typ.	75	X
$R_{DS(ON)}$	typ.	7.0	m Ω
	max.	9.0	m Ω
I_D		75	A

100% UIS TESTED!



HC!&) & top view GW Ya UĭWXJUĭ fUa

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM75Nĭ Ĩ S	HM75Nĭ Ĩ S	TO-18			-

Table 1. Absolute Maximum Ratings (TA=25°C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	75	V
Gate-Source Voltage ($V_{DS}=0V$)	V_{GS}	± 25	V
Drain Current (DC) at $T_c=25^\circ C$	$I_{D(DC)}$	ĭ Ĩ	A
Drain Current (DC) at $T_c=100^\circ C$	$I_{D(DC)}$	60	A
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_{DM(pluse)}$	300	A
Peak diode recovery voltage	dv/dt	30	V/ns
Maximum Power Dissipation($T_c=25^\circ C$)	P_D	170	W
Derating factor		1.13	W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	580	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.EAS condition: $T_J=25^\circ C, V_{DD}=50V, V_G=10V, L=0.3mH, I_D=62A$;

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.88	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	63	$^{\circ}C/W$

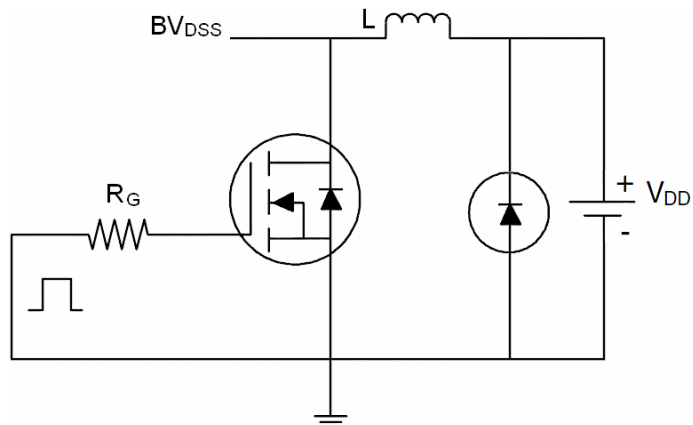
Table 3. Electrical Characteristics (TA=25 $^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	75	84		V
Zero Gate Voltage Drain Current(Tc=25 $^{\circ}C$)	I_{DSS}	$V_{DS}=75V, V_{GS}=0V$			1	μA
Zero Gate Voltage Drain Current(Tc=125 $^{\circ}C$)	I_{DSS}	$V_{DS}=75V, V_{GS}=0V$			10	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.85	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=40A$	100mΩ to 150mΩ			m Ω
Dynamic Characteristics						
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=30A$		66		S
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$		4400		PF
Output Capacitance	C_{oss}			340		PF
Reverse Transfer Capacitance	C_{rss}			260		PF
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=30A,$ $V_{GS}=10V$		100		nC
Gate-Source Charge	Q_{gs}			20		nC
Gate-Drain Charge	Q_{gd}			30		nC
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$		17.8		nS
Turn-on Rise Time	t_r			11.8		nS
Turn-Off Delay Time	$t_{d(off)}$			56		nS
Turn-Off Fall Time	t_f			14.6		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}		100A to 150A			A
Pulsed Source-drain current(Body Diode)	I_{SDM}				320	A
Forward on voltage ^(Note 1)	V_{SD}	$T_j=25^{\circ}C, I_{SD}=40A, V_{GS}=0V$			1.2	V
Reverse Recovery Time ^(Note 1)	t_{rr}	$T_j=25^{\circ}C, I_F=75A, di/dt=100A/\mu s$			36	nS
Reverse Recovery Charge ^(Note 1)	Q_{rr}					56
Forward Turn-on Time	t_{on}	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

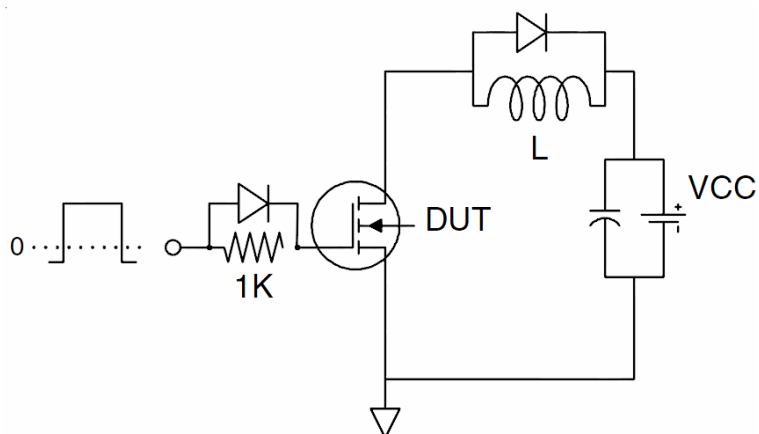
Notes 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1.5\%$, $R_G=25\Omega$, Starting $T_j=25^{\circ}C$

Test circuit

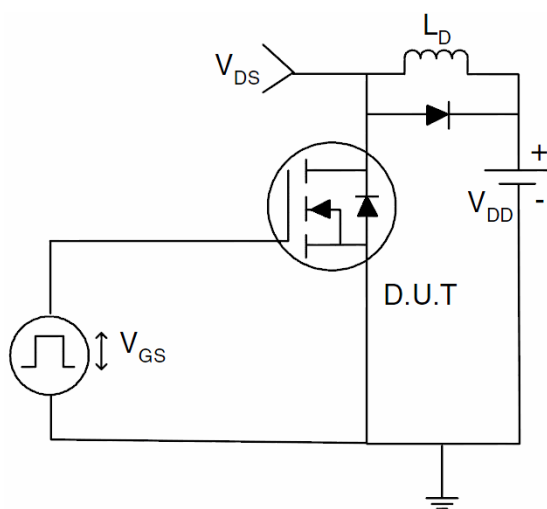
1) E_{AS} test circuits



2) Gate charge test circuit:



3) Switch Time Test Circuit:



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

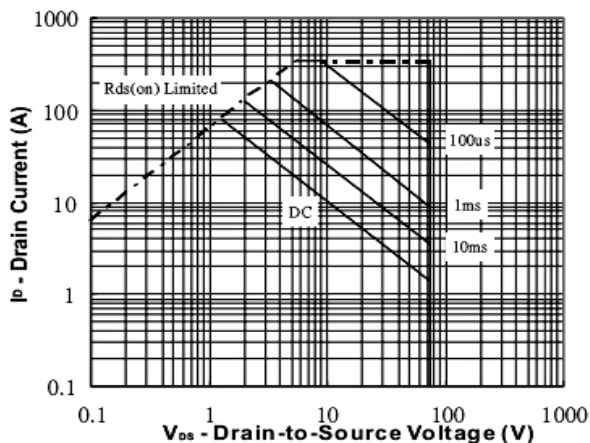


Figure2. Source-Drain Diode Forward Voltage

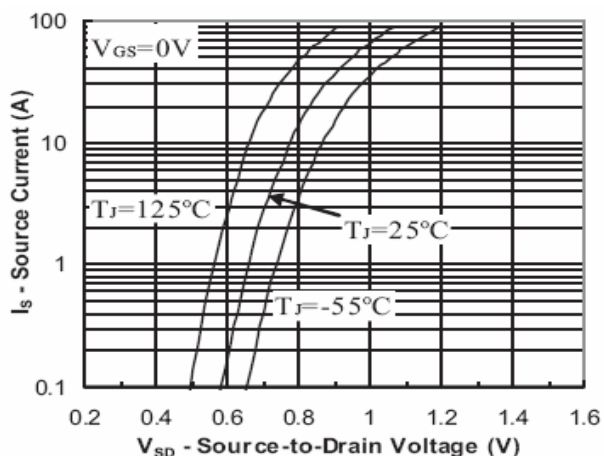


Figure3. Output characteristics

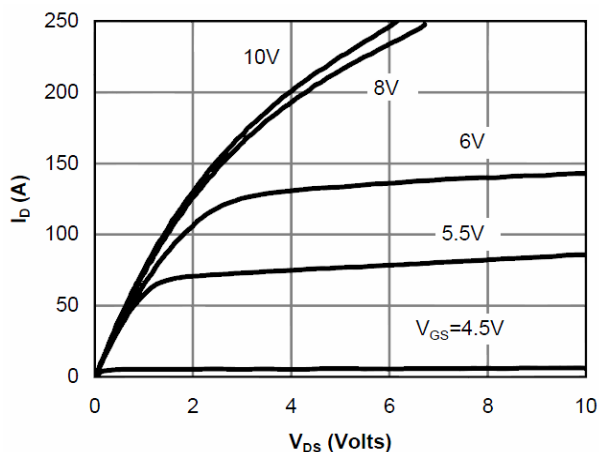


Figure4. Transfer characteristics

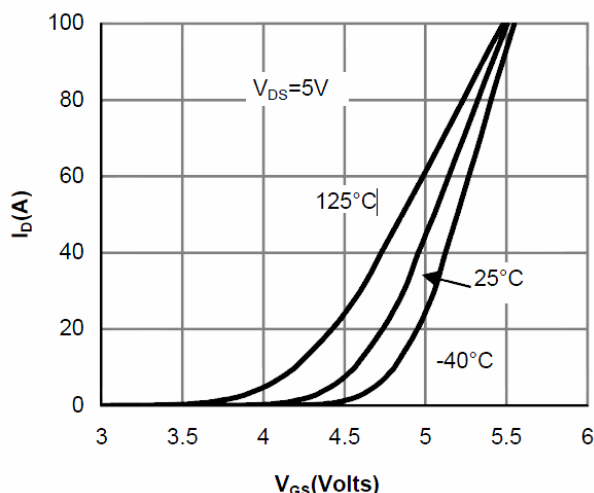


Figure5. Static drain-source on resistance

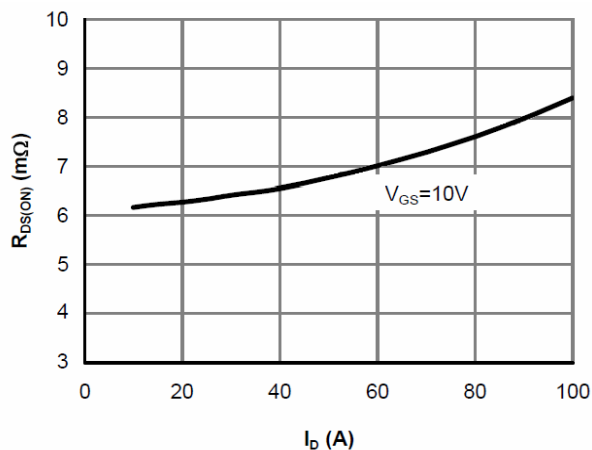


Figure6. RDS(ON) vs Junction Temperature

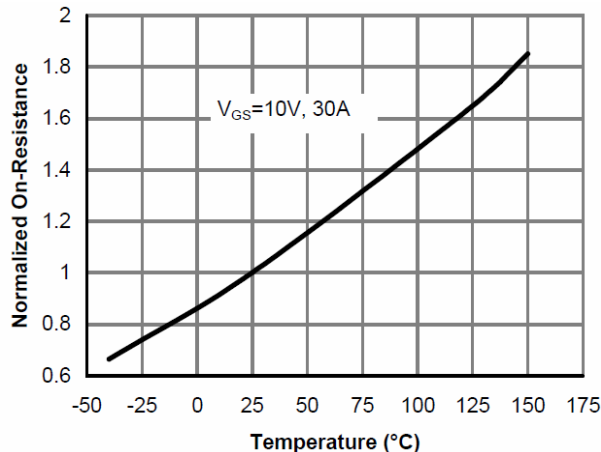


Figure7. BV_{DSS} vs Junction Temperature

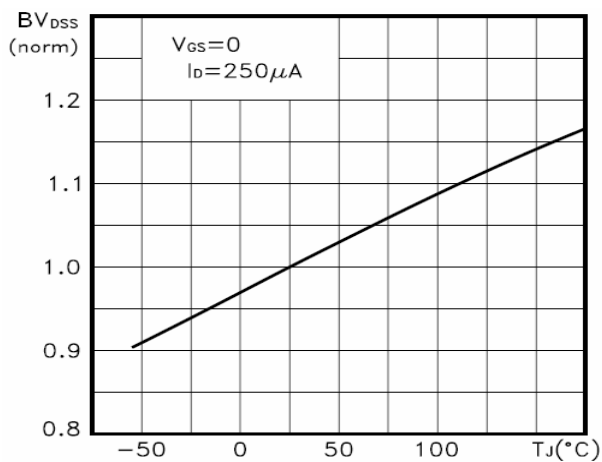


Figure8. $V_{GS(th)}$ vs Junction Temperature

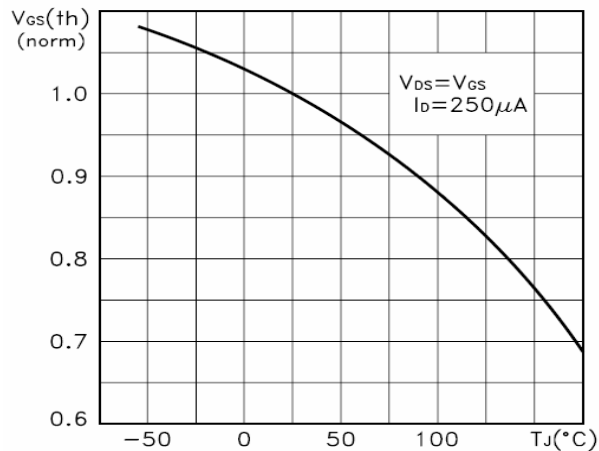


Figure9. Gate charge waveforms

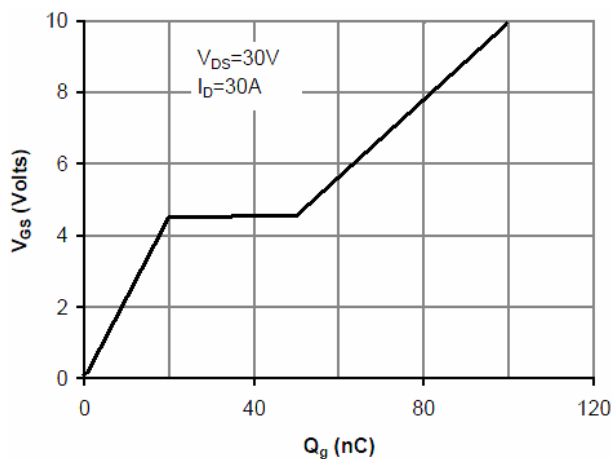
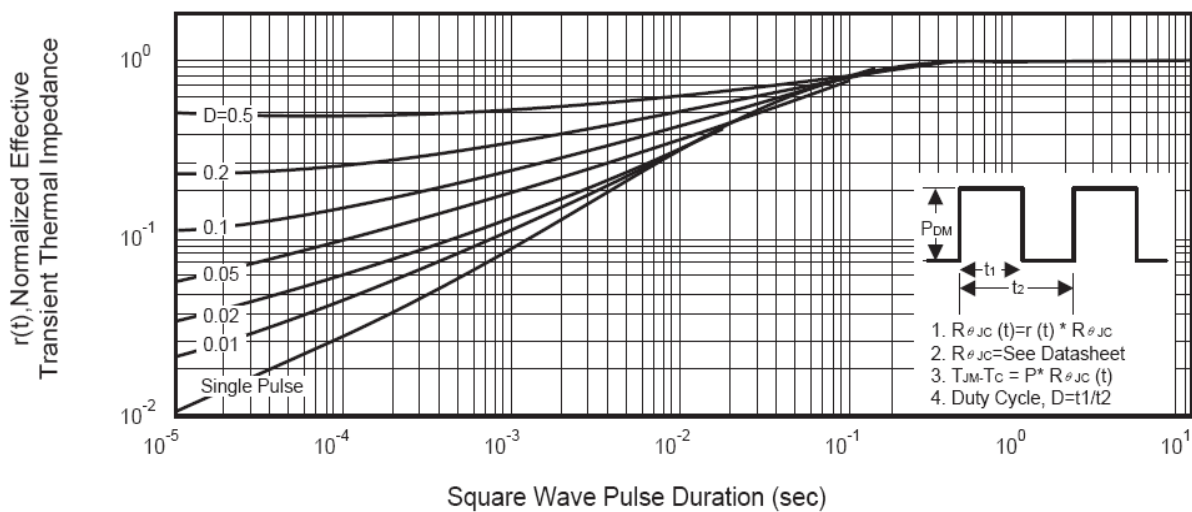
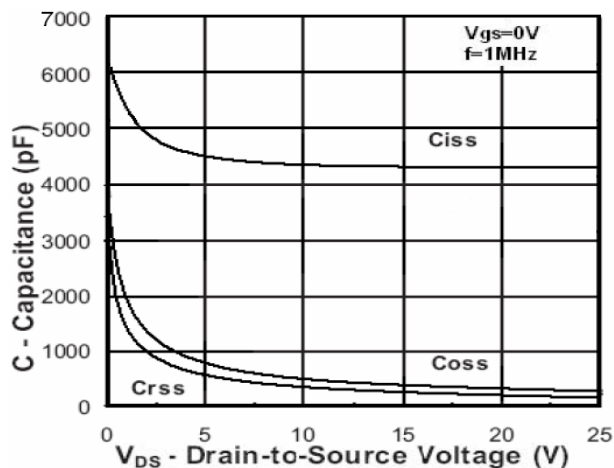
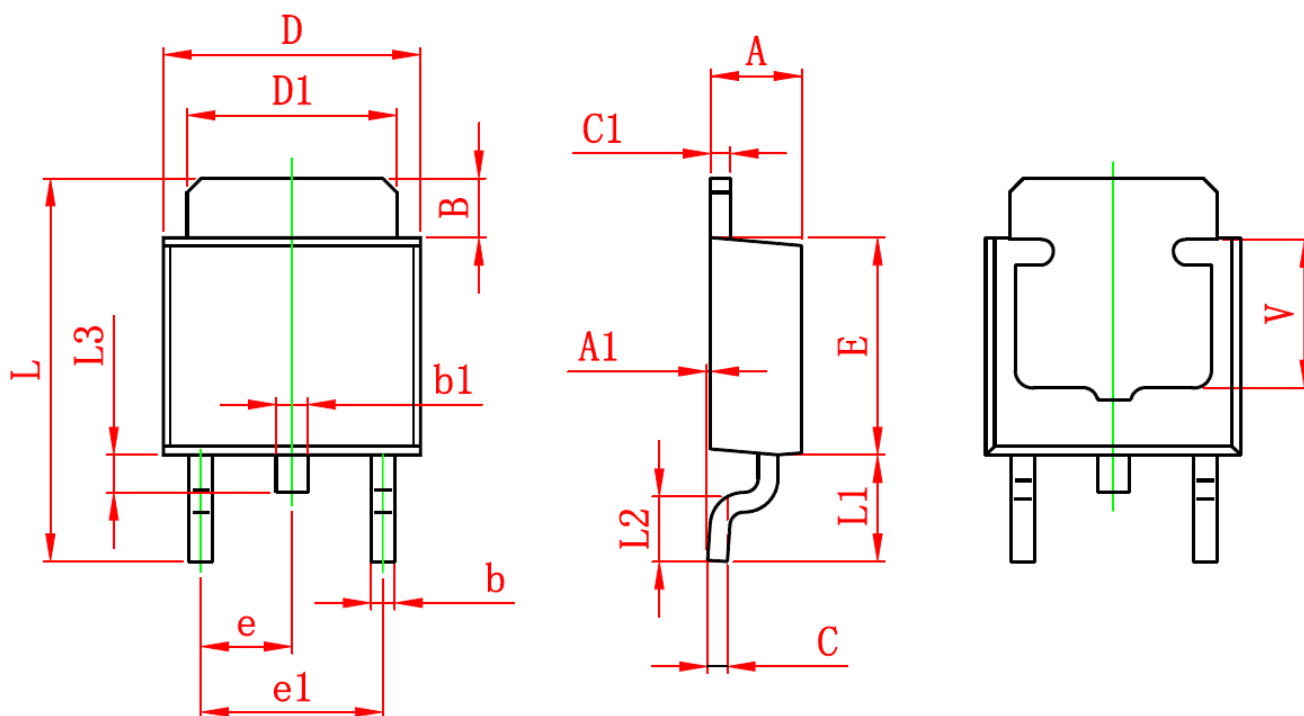


Figure10. Capacitance



TO-252-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

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